

Silicon NPN Darlington Power Transistors

2SD2493

DESCRIPTION

- With TO-3PN package
- Complement to type 2SB1624

APPLICATIONS

- Audio ,series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

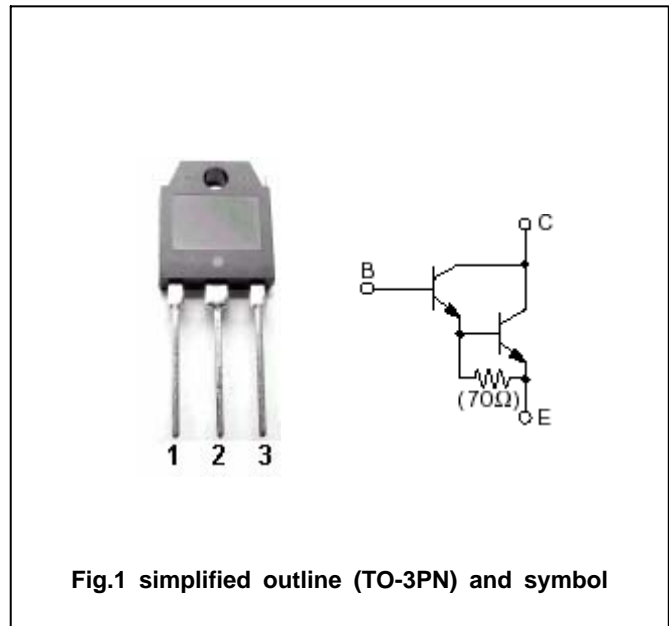


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	110	V
V_{CEO}	Collector-emitter voltage	Open base	110	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25$	60	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

Silicon NPN Darlington Power Transistors

2SD2493

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30mA ; I_B=0$	110			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=5mA$			2.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A ; I_B=5mA$			3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=110V ; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=5A ; V_{CE}=4V$	5000			
C_{ob}	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$		55		pF
f_T	Transition frequency	$I_C=2A ; V_{CE}=12V$		60		MHz

Switching times

t_{on}	Turn-on time	$I_C=5A ; R_L=6$ $I_{B1}=- I_{B2}=5mA$ $V_{CC}=30V$		0.8		μs
t_s	Storage time			6.2		μs
t_f	Fall time			1.1		μs

◆ **h_{FE} Classifications**

O	P	Y
5000-12000	6500-20000	15000-30000

Silicon NPN Darlington Power Transistors

2SD2493

PACKAGE OUTLINE

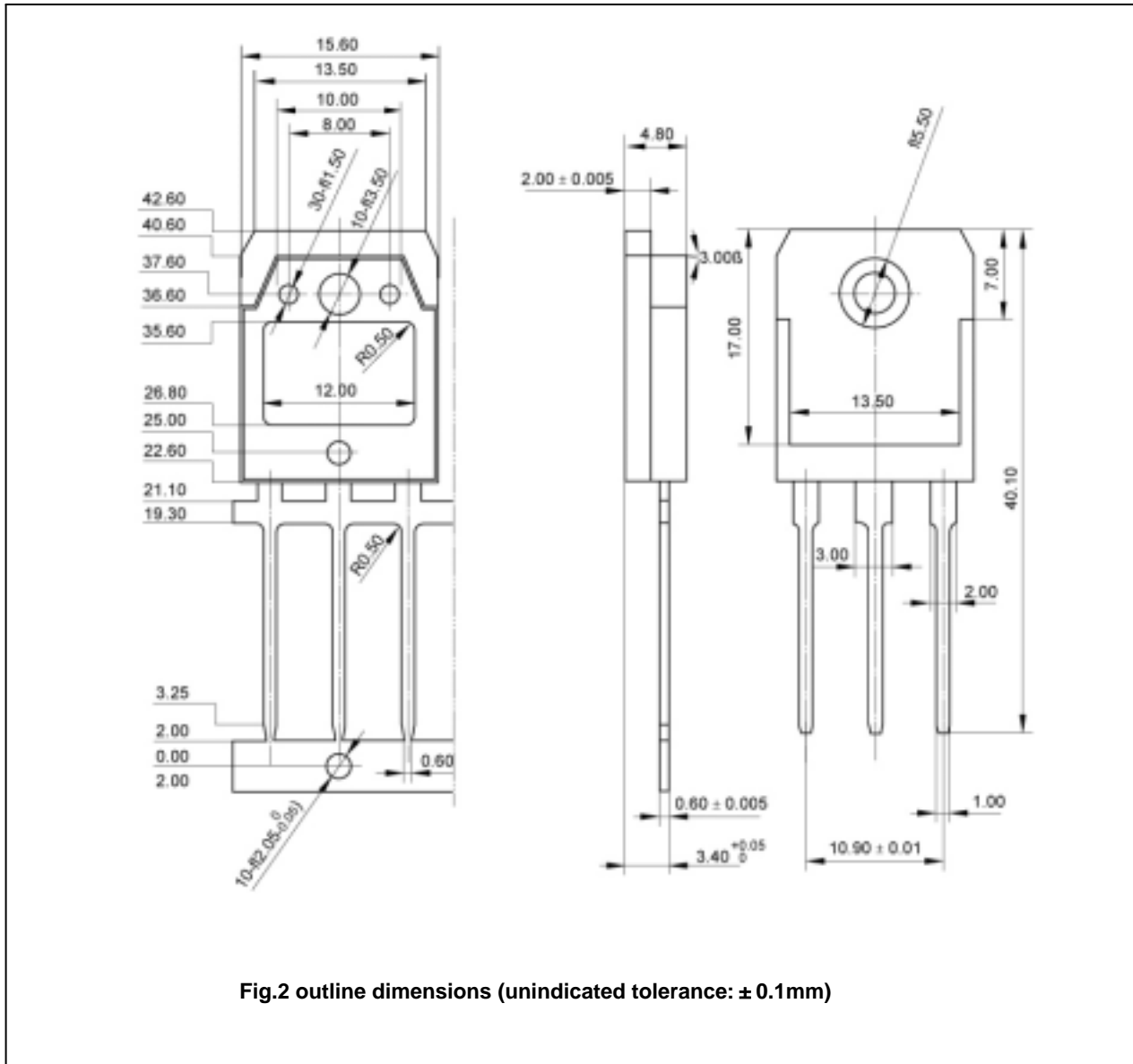


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)